

Silicon Epitaxial Planar Diode

FEATURES

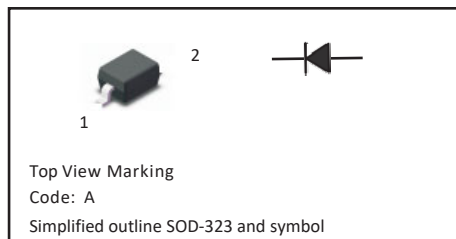
- ◆ Small surface mounting
- ◆ High Speed $t_f=1.2ns$ Ty
- ◆ High Reliability with High Surge current handling capability
- ◆ High speed switching

MECHANICAL DATA

- ◆ Case: SOD-323
- ◆ Terminals: Solderable per MIL-STD-750, Method 2026
- ◆ Approx. Weight: 5.48mg / 0.00019oz

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Maximum Ratings and Electrical characteristics

Ratings at 25 ° C ambient temperature unless otherwise specified.

Parameter	Symbols	1SS355AT	Units
Non-Repetitive Peak reverse voltage	VRM	90	V
DC Reverse Voltage	VR	80	V
Peak forward Current	IFM	225	mA
Average Rectified Output Current	IO	100	mA
Surge current (1s)	Isurge	500	mA
Operating and Storage Temperature Range	Tj, Tstg	-55 ~ 125	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbols	1SS355AT	Units
Forward voltage $I_F=100mA$	VF	1.2	V
Reverse current $V_R=80V$	IR	0.1	μA
Capacitance between terminals $V_R=0.5V$ $f=1MHz$	CT	3	pF
Reverse Recovery Time $I_F=10mA, V_R=6V, R_L=100\Omega$	trr	4	ns

Fig.1 FORWARD CHARACTERISTICS

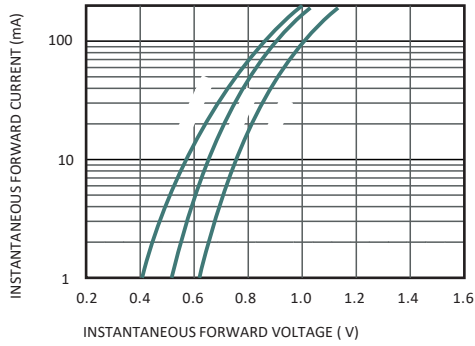


Fig.2 Typical Reverse Characteristics

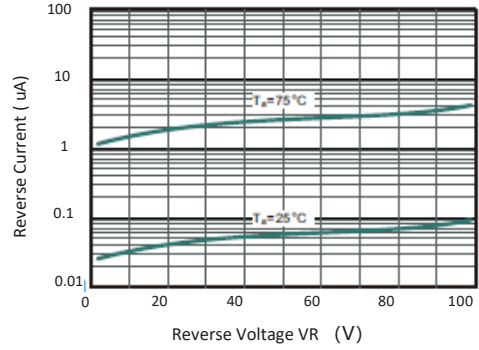
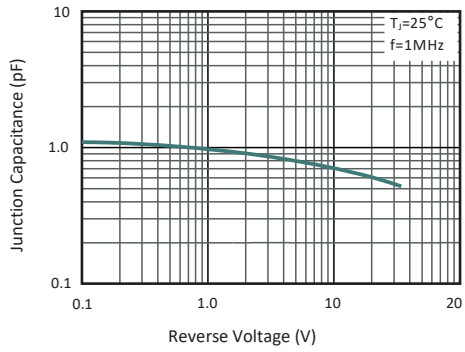


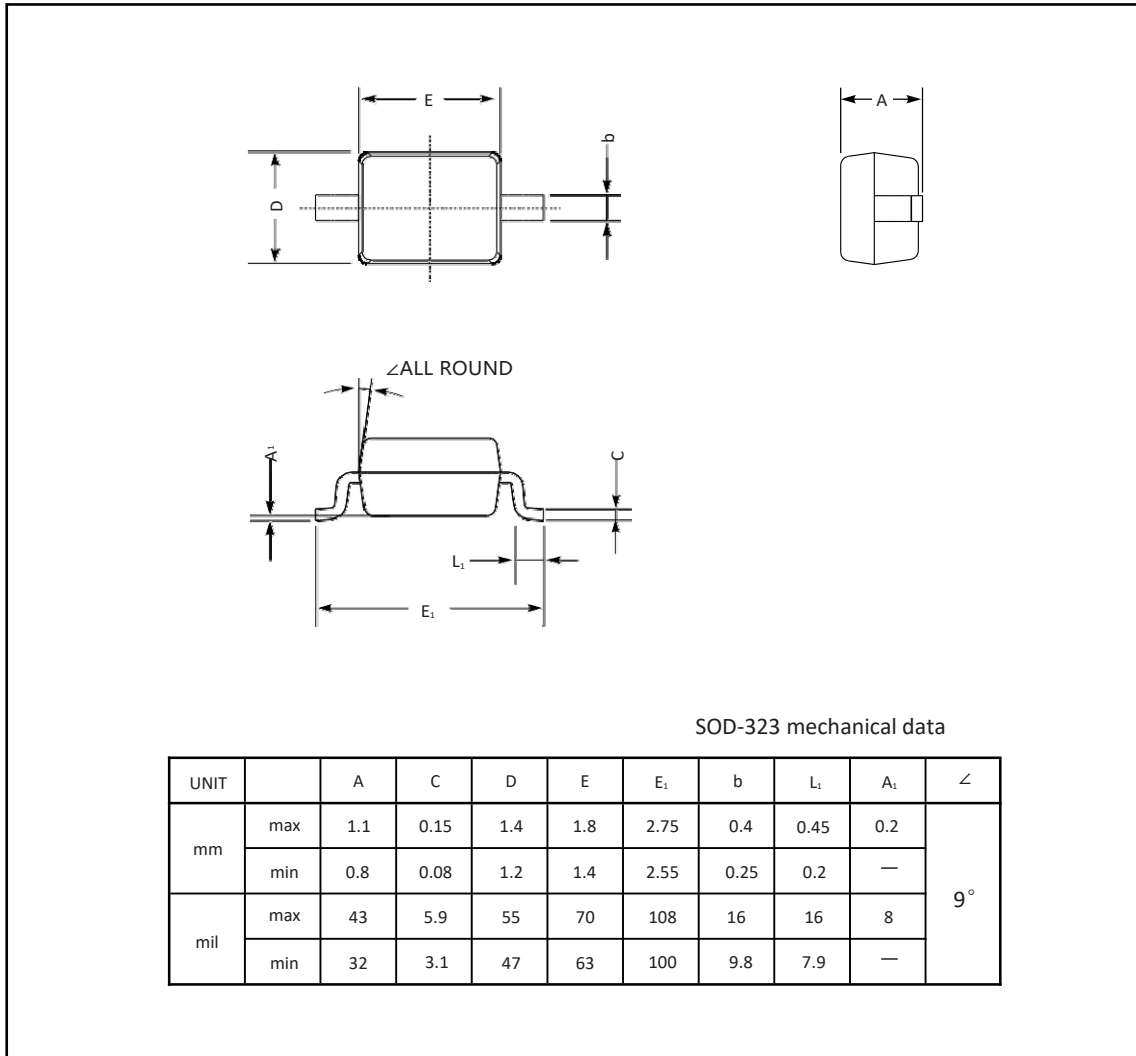
Fig.3 Typical Junction Capacitance



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



The recommended mounting pad size

